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FORM

(to be used for all correspondence after initial filing)

Total Number of Pages in This Submission

Application Number 10/615,051

Filing Date July 7, 2003

First Named Inventor Brian A. Vaartstra

Art Unit 2812

Examiner Name Unknown

Attorney Docket Number MI22-2308

ENCLOSURES (Check all that apply)

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| <input type="checkbox"/> Response to Missing Parts/Incomplete Application | | |
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Remarks

EV372470700

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SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT

 Firm or Individual Mark S. Matkin, Reg. No. 32,268
Wells St. John, P.S.

Signature

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CERTIFICATE OF TRANSMISSION/MAILING

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application Serial No. 10/615,051
Filing Date July 7, 2003
Inventorship Brian A. Vaartstra
Assignee Micron Technology, Inc.
Group Art Unit 2812
Examiner Unknown
Attorney's Docket No. MI22-2308
Customer No. 021567
Title: Methods of Forming a Phosphorus Doped Silicon Dioxide Comprising Layer, and Methods of Forming Trench Isolation in the Fabrication of Integrated Circuitry

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

References - See Attached Form PTO-1449

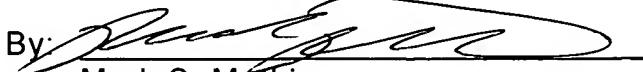
In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, your attention is directed to the United States patents and other references listed on the attached Form PTO-1449. Copies of the cited art are attached hereto. No admission is made regarding whether all the submitted references are prior art.

This Supplemental Information Disclosure Statement is being filed within three months of the filing date of the application or before the mailing of a first Office Action on the merits, whichever occurs last. Therefore, no fee is believed to be required. However, in the event that a fee is required for filing this Supplemental Information Disclosure Statement, please charge the fee specified under 37 C.F.R. § 1.17(p) to Deposit Account No. 23-0925.

EV372470700

Respectfully submitted,

Dated: 11-17-04

By: 
Mark S. Matkin
Reg. No. 32,268

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| FILING DATE July 7, 2003 | GROUP ART UNIT 2812 | |

| U.S. PATENT DOCUMENTS | | | | | | | |
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| | | | | | | | Yes No |
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| EXAMINER | DATE CONSIDERED | |

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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| Form PTO-144 PATENT & TRADEMARK OFFICE LIST OF ART CITED BY APPLICANT (Use several sheets if necessary) | | ATTY. DOCKET NO. MI22-2308 | SERIAL NO. 10/615,051 |
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| | | FILING DATE July 7, 2003 | GROUP ART UNIT 2812 |

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| | AL | | | | | |

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| ART CITED BY APPLICANT (Use several sheets if necessary) | | APPLICANT: Brian A. Vaarstra | | | |
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| | | APPLICANT: Brian A. Vaarstra | | |
| | | FILING DATE July 7, 2003 | GROUP 2812 | |

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| | AJ | | | | | | No |

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| | | LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary) | | APPLICANT: Brian A. Vaarstra | |
| | | | | FILING DATE July 7, 2003 | GROUP 2812 |

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| | | Document Number | Date | Country | Class | Subclass | Translation |
| | | | | | | | Yes |
| | AJ | | | | | | No |

EV372470700

| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
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